MMT05B230T3, MMT05B260T3, MMT05B310T3

Preferred Device

Thyristor Surge Protectors

High Voltage Bidirectional TSPD

These Thyristor Surge Protective devices (TSPD) prevent overvoltage damage to sensitive circuits by lightning, induction and power line crossings. They are breakover–triggered crowbar protectors. Turn–off occurs when the surge current falls below the holding current value.

Secondary protection applications for electronic telecom equipment at customer premises.

- High Surge Current Capability: 50 Amps 10 x 1000 μsec Guaranteed at the extended temp range of –20°C to 65°C
- The MMT05B230T3 Series is used to help equipment meet various regulatory requirements including: Bellcore 1089, ITU K.20 & K.21, IEC 950, UL 1459 & 1950 and FCC Part 68.
- Bidirectional Protection in a Single Device
- Little Change of Voltage Limit with Transient Amplitude or Rate
- Freedom from Wearout Mechanisms Present in Non–Semiconductor Devices
- Fail–Safe, Shorts When Overstressed, Preventing Continued Unprotected Operation.
- Surface Mount Technology (SMT)
- Ⓤ Indicates UL Registered — File #E116110
- Device Marking: Logo, MMT05B230T3: RPBF; MMT05B260T3: RPBG; MMT05B310T3: RPBJ, and Date Code

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Off–State Voltage — Maximum MMT05B230T3 MMT05B260T3 MMT05B310T3	V_{DM}	 ±170 ±200 ±270	Volts
Maximum Pulse Surge Short Circuit Current Non–Repetitive Double Exponential Decay Waveform Notes 1, 2 10 x 1000 μsec (–20°C to +65°C) 8 x 20 μsec 10 x 160 μsec 10 x 560 μsec	 I_{PPS1} I_{PPS2} I_{PPS3} I_{PPS4}	 ±50 ±150 ±100 ±70	A(pk)
Maximum Non–Repetitive Rate of Change of On–State Current Double Exponential Waveform, R = 1.0, L = 1.5 μH, C = 1.67 μF, I_{pk} = 110A	di/dt	±150	A/μs

ON Semiconductor

http://onsemi.com

BIDIRECTIONAL TSPD (Ⓤ)
50 AMP SURGE
265 thru 365 VOLTS

SMB
(No Polarity)
(Essentially JEDEC DO–214AA)
CASE 403C

ORDERING INFORMATION

Device	Package	Shipping
MMT05B230T3	SMB	12mm Tape and Reel (2.5K/Reel)
MMT05B260T3	SMB	12mm Tape and Reel (2.5K/Reel)
MMT05B310T3	SMB	12mm Tape and Reel (2.5K/Reel)

Preferred devices are recommended choices for future use and best overall value.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Operating Temperature Range Blocking or Conducting State	T_{J1}	–40 to +125	°C
Overload Junction Temperature — Maximum Conducting State Only	T_{J2}	+175	°C
Instantaneous Peak Power Dissipation (I_{pk} = 50A, 10x1000 μsec @ 25°C)	P_{PK}	2000	W
Maximum Lead Temperature for Soldering Purposes 1/8″ from Case for 10 Seconds	T_L	260	°C

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Devices are bidirectional. All electrical parameters apply to forward and reverse polarities.

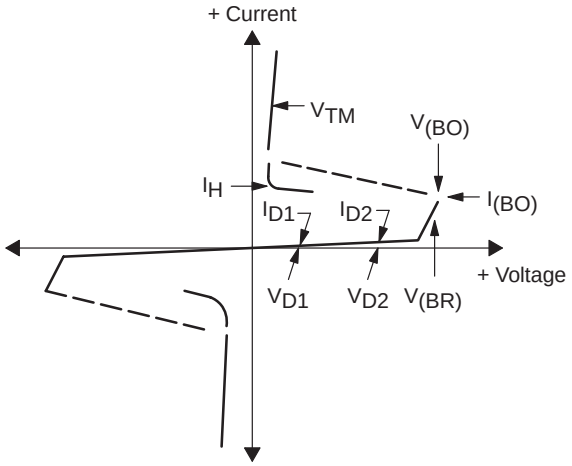
Characteristics		Symbol	Min	Typ	Max	Unit
Breakover Voltage (Both polarities)		$V_{(BO)}$				Volts
(dv/dt = 100 V/μs, I_{SC} = 1.0 A, Vdc = 1000 V)	MMT05B230T3		—	—	265	
	MMT05B260T3		—	—	320	
	MMT05B310T3		—	—	365	
(+65°C)						
	MMT05B230T3		—	—	280	
	MMT05B260T3		—	—	340	
	MMT05B310T3		—	—	400	
Breakover Voltage (Both polarities)		$V_{(BO)}$				Volts
(f = 60 Hz, I_{SC} = 1.0 A(rms), V_{OC} = 1000 V(rms),	MMT05B230T3		—	—	265	
R_I = 1.0 kΩ, t = 0.5 cycle, Note 2)	MMT05B260T3		—	—	320	
	MMT05B310T3		—	—	365	
(+65°C)						
	MMT05B230T3		—	—	280	
	MMT05B260T3		—	—	340	
	MMT05B310T3		—	—	400	
Breakover Voltage Temperature Coefficient		$dV_{(BO)}/dT_J$	—	0.08	—	%/°C
Breakdown Voltage ($I_{(BR)}$ = 1.0 mA) Both polarities		$V_{(BR)}$				Volts
	MMT05B230T3		—	190	—	
	MMT05B260T3		—	240	—	
	MMT05B310T3		—	280	—	
Off State Current (V_{D1} = 50 V) Both polarities		I_{D1}	—	—	2.0	μA
(V_{D2} = V_{DM}) Both polarities		I_{D2}	—	—	5.0	
On–State Voltage (I_T = 1.0 A)		V_T	—	1.53	3.0	Volts
(PW ≤ 300 μs, Duty Cycle ≤ 2%, Note 2)						
Breakover Current (f = 60 Hz, V_{DM} = 1000 V(rms), R_S = 1.0 kΩ)		I_{BO}	—	230	—	mA
Both polarities						
Holding Current (Both polarities)	Note 2	I_H	175	340	—	mA
V_S = 500 Volts; I_T (Initiating Current) = ±1.0 Amp	(+65°C)		130	—	—	
Critical Rate of Rise of Off–State Voltage		dv/dt	2000	—	—	V/μs
(Linear waveform, V_D = Rated V_{BR}, T_J = 25°C)						
Capacitance (f = 1.0 MHz, 50 Vdc, 1.0 V rms Signal)		C_O	—	22	—	pF
(f = 1.0 MHz, 2.0 Vdc, 15 mV rms Signal)			—	53	75	

(1) Allow cooling before testing second polarity.

(2) Measured under pulse conditions to reduce heating.

Voltage Current Characteristic of TSPD (Bidirectional Device)

Symbol	Parameter
I_{D1}, I_{D2}	Off State Leakage Current
V_{D1}, V_{D2}	Off State Blocking Voltage
V_{BR}	Breakdown Voltage
V_{BO}	Breakover Voltage
I_{BO}	Breakover Current
I_H	Holding Current
V_{TM}	On State Voltage



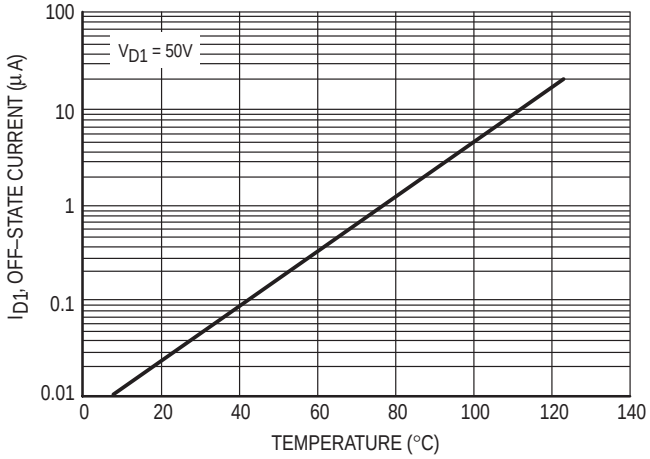


Figure 1. Off–State Current versus Temperature

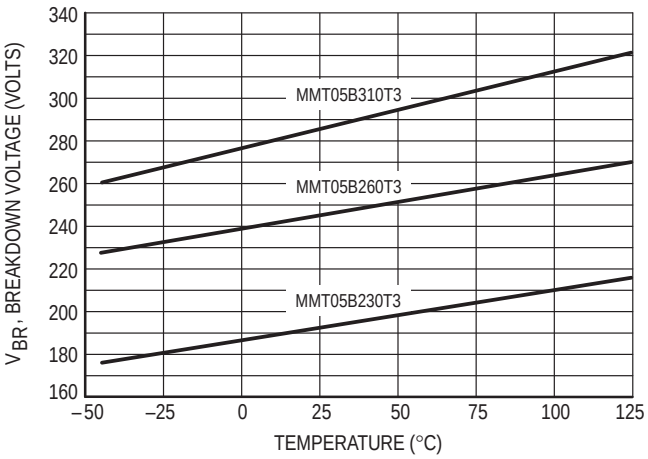


Figure 2. Breakdown Voltage versus Temperature

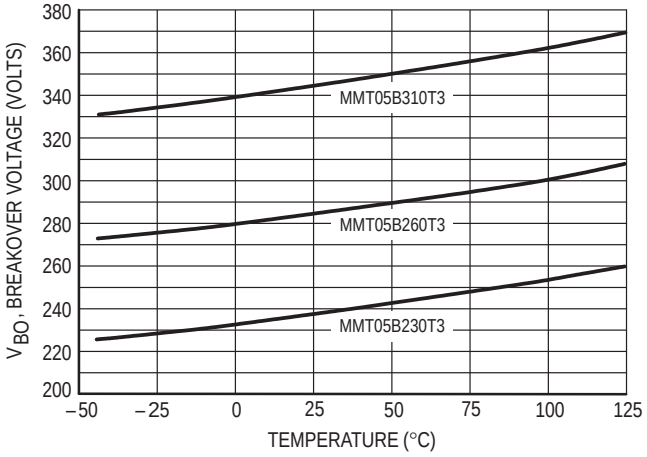


Figure 3. Breakover Voltage versus Temperature

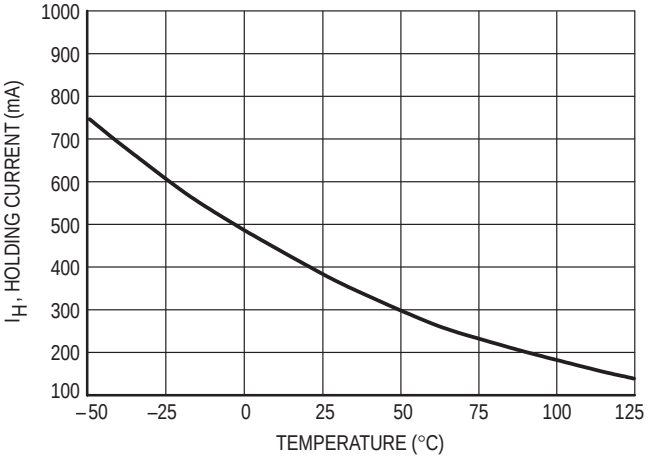


Figure 4. Holding Current versus Temperature

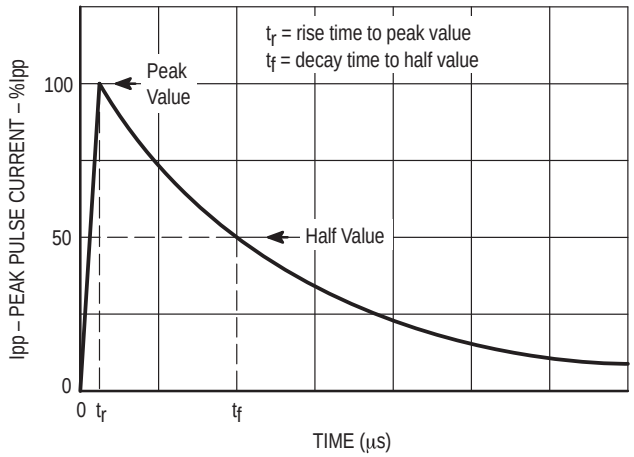


Figure 5. Exponential Decay Pulse Waveform

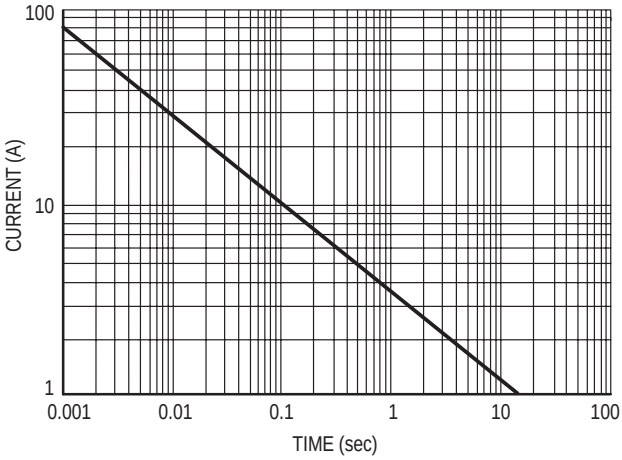
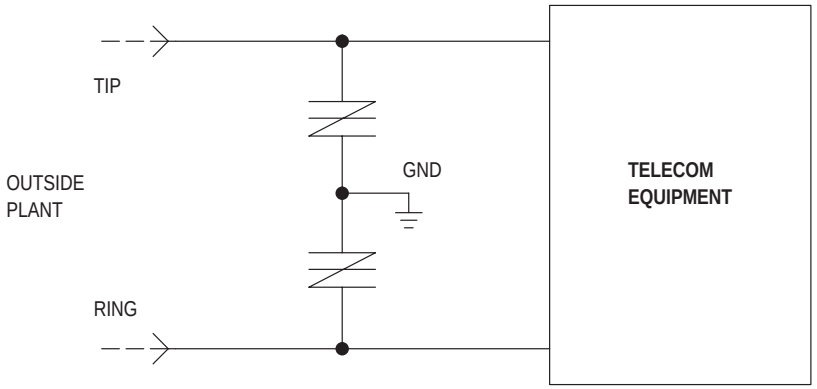
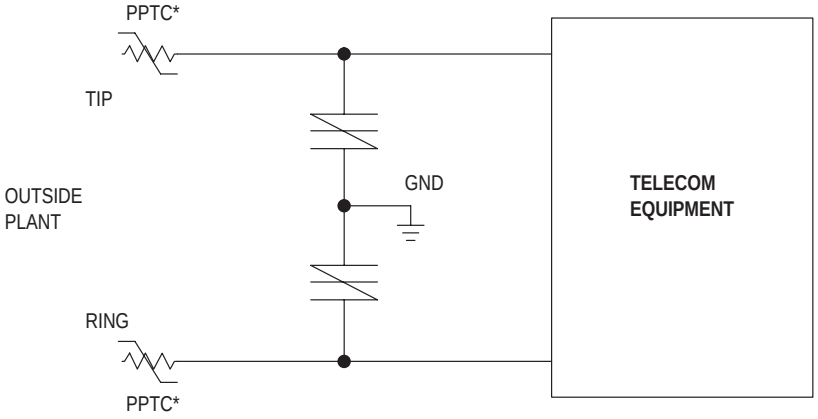
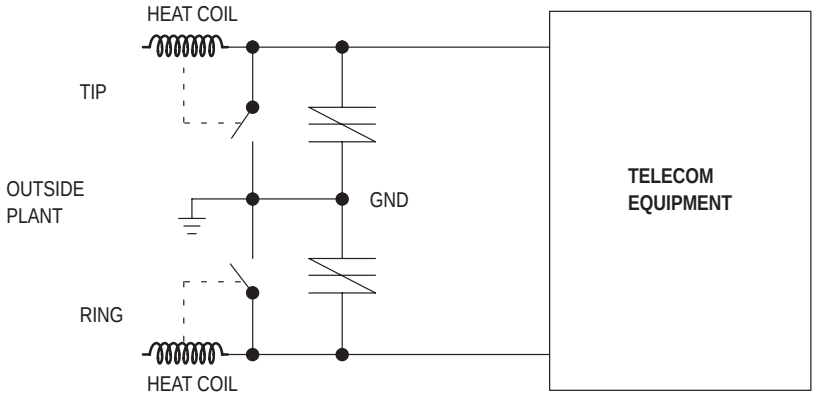


Figure 6. Peak Surge On–State Current versus Surge Current Duration, Sinusoidal Waveform



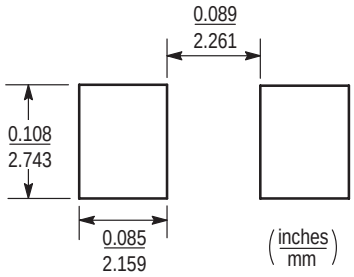


*Polymeric PTC (positive temperature coefficient) overcurrent protection device



MINIMUM RECOMMENDED FOOTPRINT FOR SURFACE MOUNTED APPLICATIONS

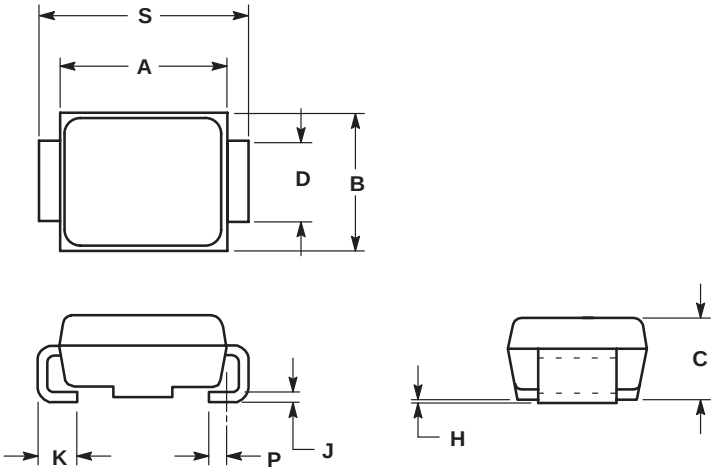
Surface mount board layout is a critical portion of the total design. The footprint for the semiconductor packages must be the correct size to insure proper solder connection interface between the board and the package. With the correct pad geometry, the packages will self align when subjected to a solder reflow process.



SMB

PACKAGE DIMENSIONS

SMB
(No Polarity)
(Essentially JEDEC DO–214AA)
CASE 403C–01
ISSUE O



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. D DIMENSION SHALL BE MEASURED WITHIN DIMENSION P.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.160	0.180	4.06	4.57
B	0.130	0.150	3.30	3.81
C	0.075	0.095	1.90	2.41
D	0.077	0.083	1.96	2.11
H	0.0020	0.0060	0.051	0.152
J	0.006	0.012	0.15	0.30
K	0.030	0.050	0.76	1.27
P	0.020 REF		0.51 REF	
S	0.205	0.220	5.21	5.59

Notes

PUBLICATION ORDERING INFORMATION

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